

Silicon N-Channel Planar Power MOSFET

Description

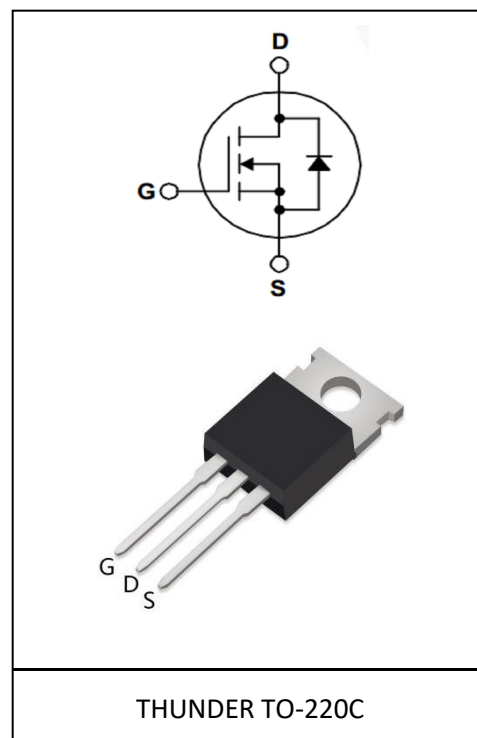
The IRF3415 utilizes the latest processing techniques to achieve low on-resistance per silicon area. Additional features of this MOSFET are 150°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications. It can be used in a wide variety of applications.

General Features

- $V_{DS}=150V, I_D=42A$
- Low ON Resistance, $R_{DS(ON)}=34m\Omega @ V_{GS}=10V, I_D=21A$
- Low reverse transfer capacitance
- Low Qg for fast response
- Short fall & rise times for fast switching
- 100% single pulse avalanche energy Test

Application

- Power switching application
- Digital amplifier
- Adapter and charger



Product Summary

V_{DS}	150V
$R_{DS(on)}$	34m Ω
I_D	42A

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	150	V
Continuous drain current $T_C = 25^\circ C$ (Silicon limit)	I_D	42	A
Pulsed drain current ($T_C = 25^\circ C$, t_p limited by T_{jmax})	I_{DM}	168	A
Avalanche energy, single pulse ($L=10mH$, $R_g=25\Omega$)	E_{AS}	1922	mJ
Gate-Source voltage	V_{GS}	± 30	V
Power dissipation ($T_C = 25^\circ C$)	P_D	167	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ C$

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.75	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	62	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	150	-	-	V	$V_{GS}=0\text{ V}, I_D=250\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2.0	-	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=150\text{ V}, V_{GS}=0\text{ V}$ $T_j=25\text{ }^{\circ}\text{C}$
		-	-	10	μA	$V_{DS}=120\text{ V}, V_{GS}=0\text{ V}$ $T_j=125\text{ }^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 30\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	34	41	m Ω	$V_{GS}=10\text{ V}, I_D=21\text{ A}$
Transconductance	g_{fs}	-	10	-	S	$V_{DS}=30\text{ V}, I_D=21\text{ A}$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	2359	-	pF	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$
Output Capacitance	C_{oss}	-	745	-		
Reverse Transfer Capacitance	C_{rss}	-	598	-		
Gate Total Charge	Q_g	-	-	210	nC	$V_{GS}=10\text{ V}, V_{DS}=120\text{ V},$ $I_D=42\text{ A}$
Gate-Source charge	Q_{gs}	-	-	15		
Gate-Drain charge	Q_{gd}	-	-	96		
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=75\text{ V}, I_D=42\text{ A},$ $R_G=25\text{ }\Omega$
Rise time	t_r	-	56	-		
Turn-off delay time	$t_{d(off)}$	-	70	-		
Fall time	t_f	-	68	-		
Gate resistance	R_G	-	1.19	-	Ω	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V},$ $f=1\text{ MHz}$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	-	1.3	V	$V_{GS}=0V, I_{DS}=42A$
Body Diode Continuous Forward Current	I_S	-	-	42	A	$T_C=25^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	255	-	ns	$T_C=25^{\circ}C, I_S=42A,$ $di/dt=100A/us$
Body Diode Reverse Recovery Charge	Q_{rr}	-	2.1	-	μC	

Typical Performance Characteristics

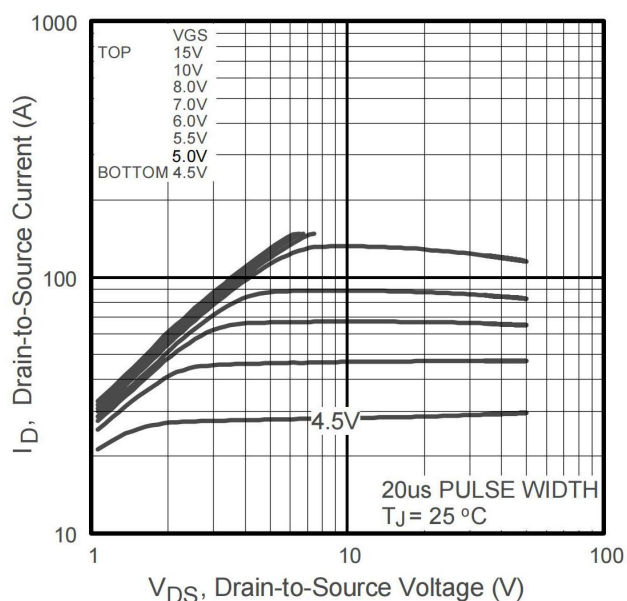


Fig 1. Typical Output Characteristics

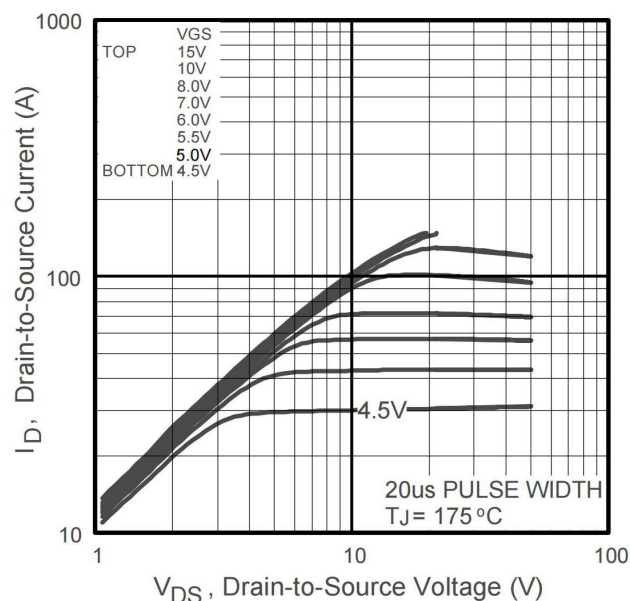


Fig 2. Typical Output Characteristics

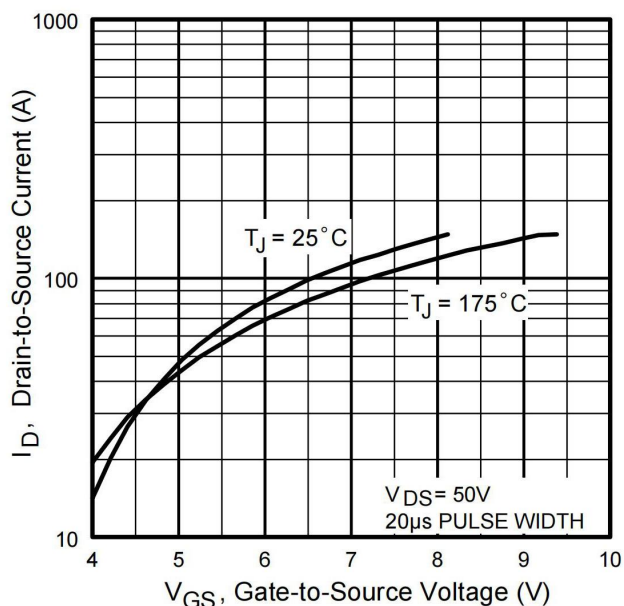


Fig 3. Typical Transfer Characteristics

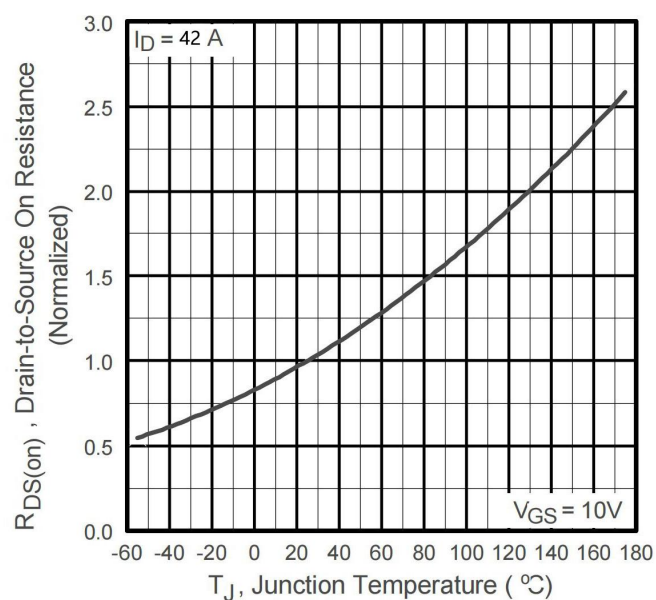


Fig 4. Normalized On-Resistance Vs. Temperature

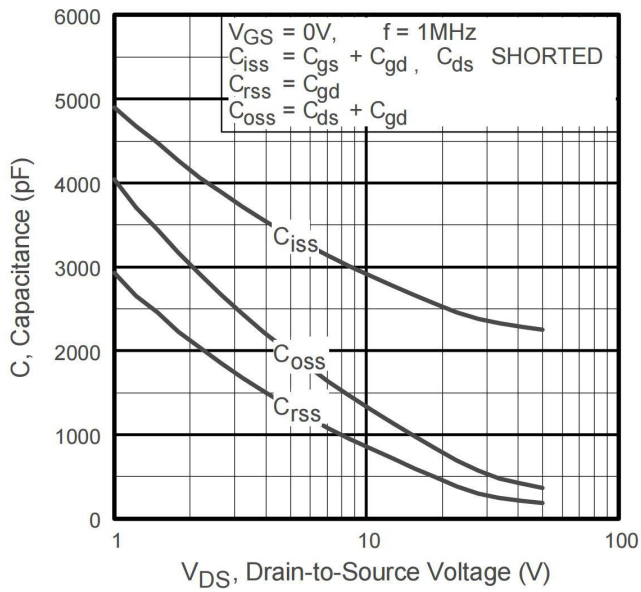


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

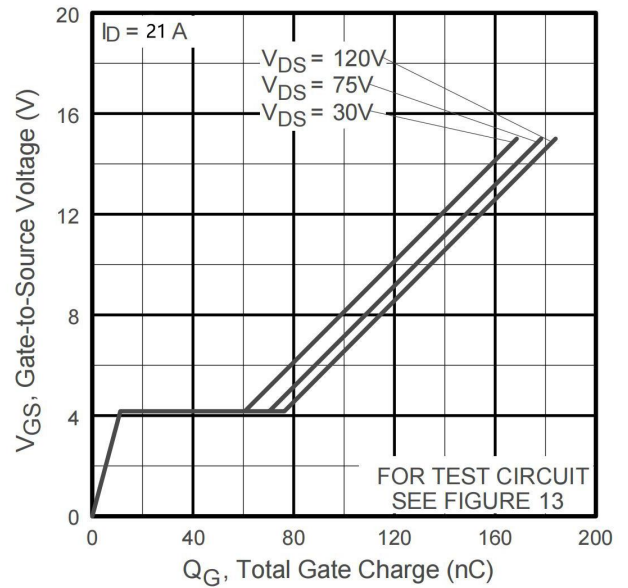


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

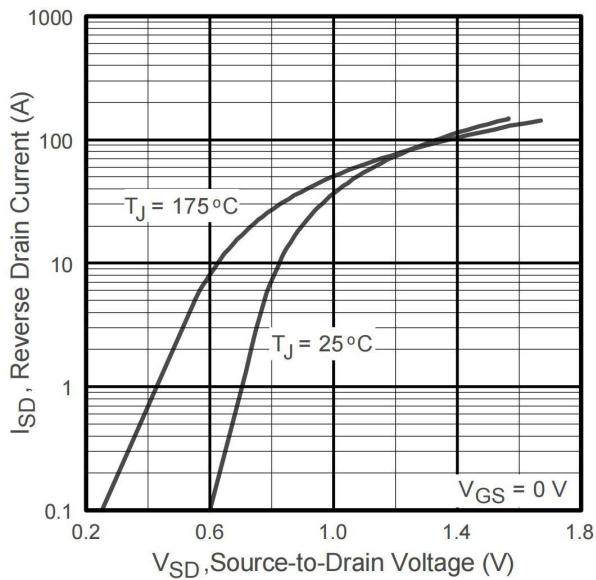


Fig 7. Typical Source-Drain Diode Forward Voltage

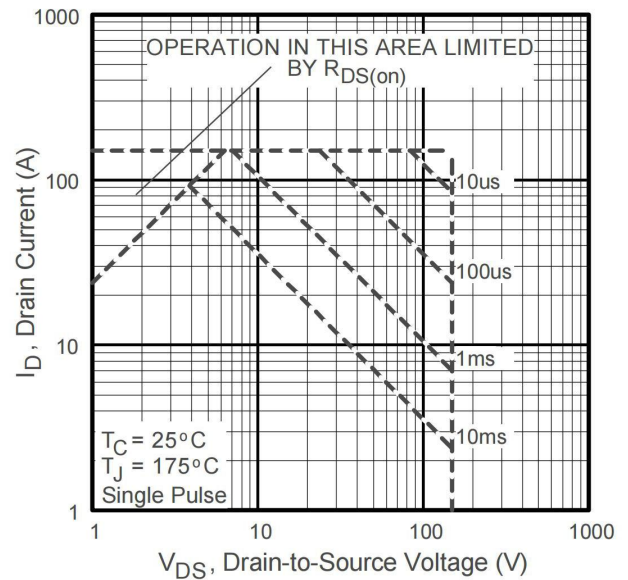


Fig 8. Maximum Safe Operating Area

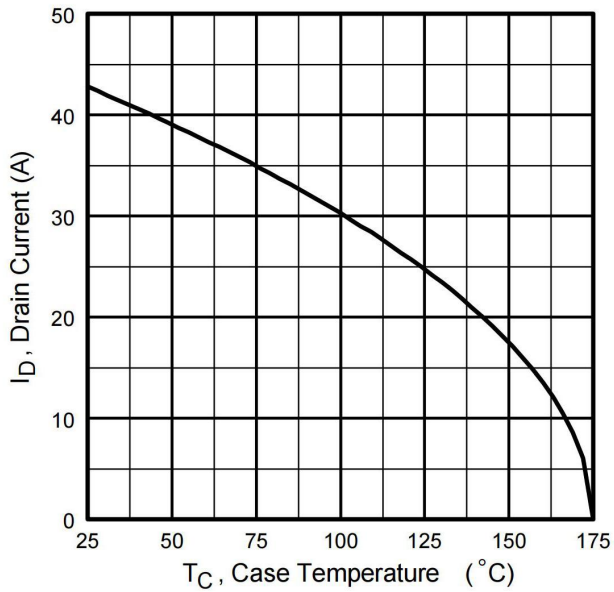


Fig 9. Maximum Drain Current Vs. Case Temperature

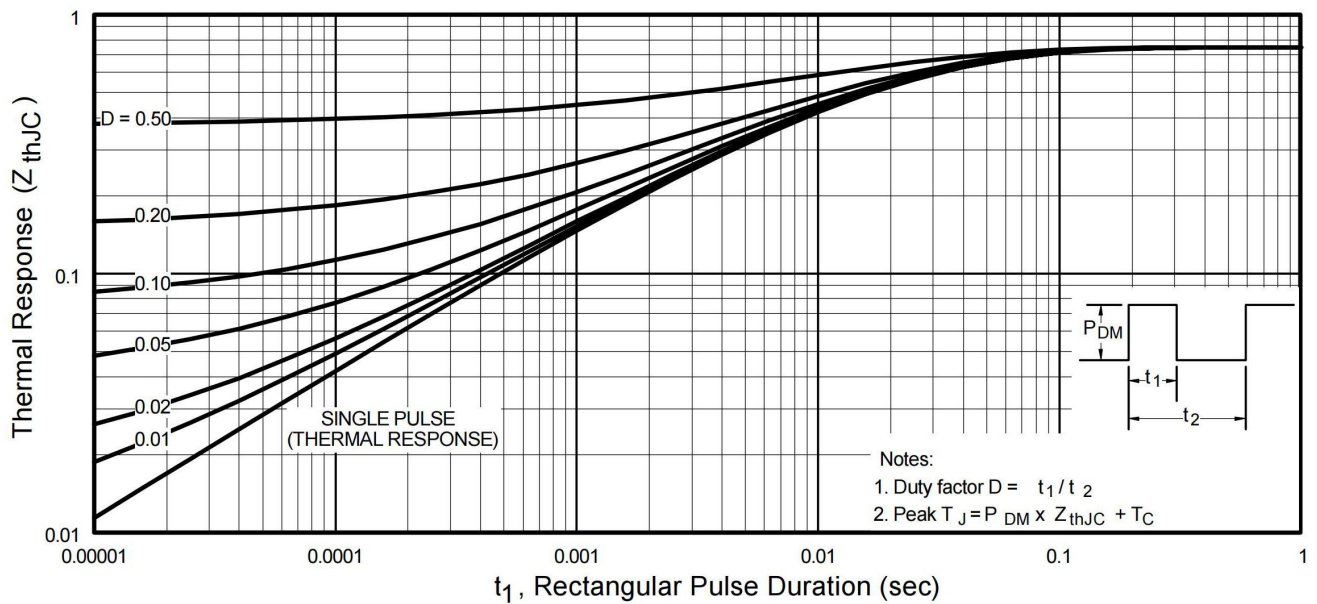
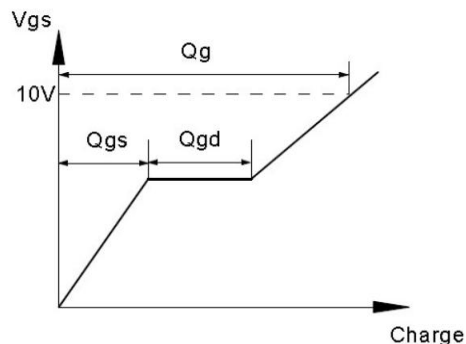
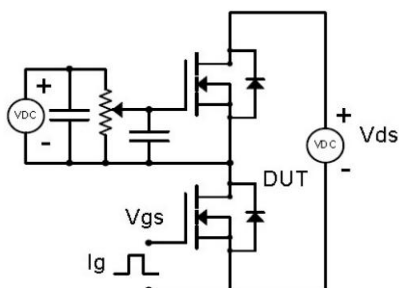


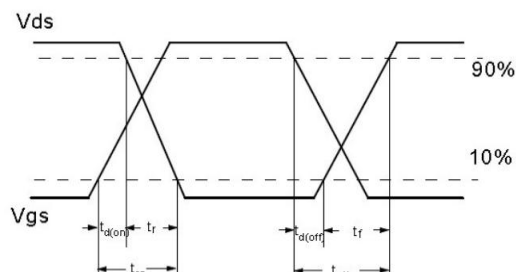
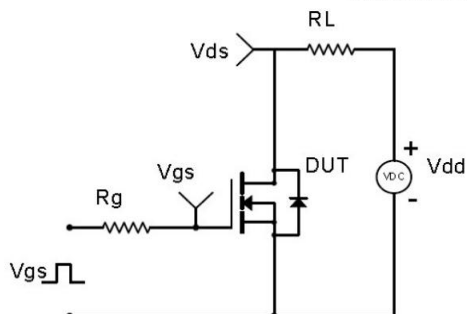
Fig 10 . Maximum Effective Transient Thermal Impedance, Junction-to-Case

Test Circuit & Waveform

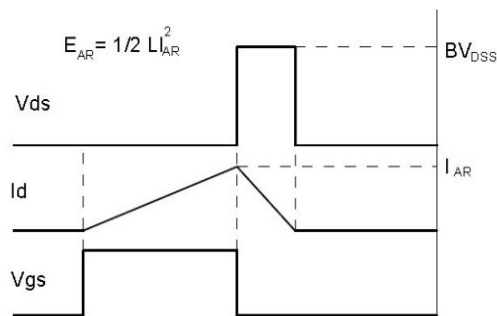
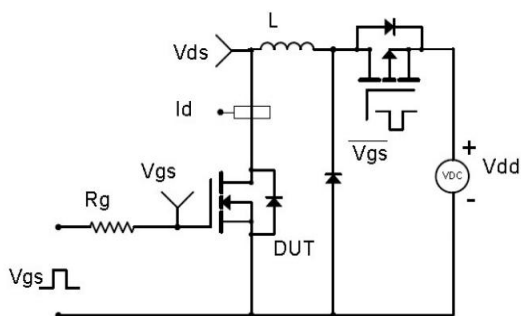
Gate Charge Test Circuit & Waveform



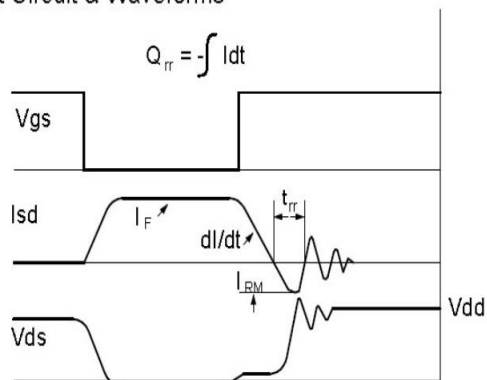
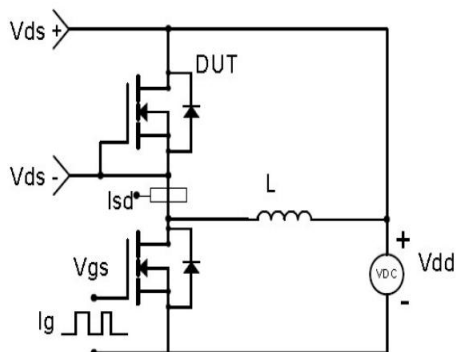
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



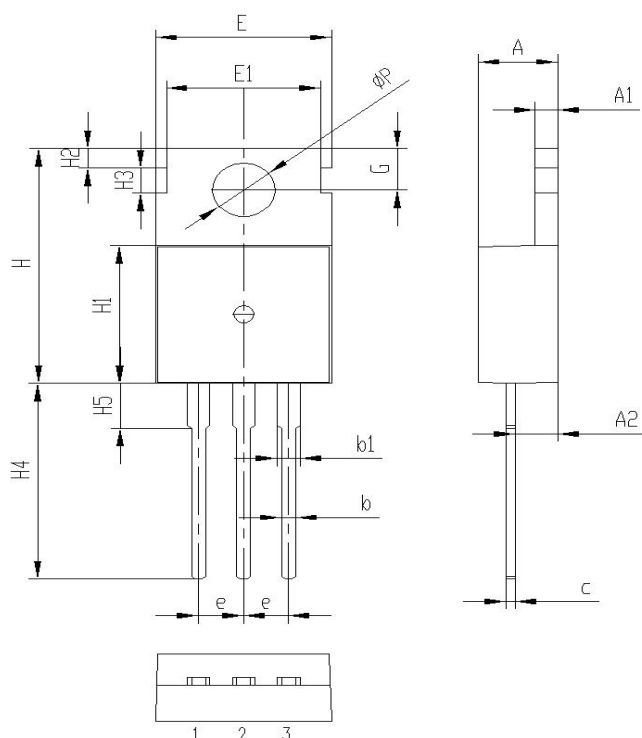
Diode Recovery Test Circuit & Waveforms



Package Information

TO-220C PACKAGE

基本尺寸



Symbol	单位 mm		
	Min	Nom	Max
A	4.30	4.5	4.70
A1	1.20	1.30	1.40
A2	2.20	2.4	2.60
b	0.60	0.8	1.00
b1	1.20	1.30	1.40
c	0.40	0.5	0.60
e	2.44	2.54	2.64
E	9.80	10.0	10.2
E1	8.50	8.70	8.90
H	15.5	15.7	15.9
H1	9.00	9.2	9.40
H2	1.10	1.34	1.50
H3	1.50	1.7	1.90
H4	12.9	13.3	13.7
H5	2.80	3.0	3.20
G	2.60	2.8	3.00
ΦP	3.40	3.6	3.80

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